

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	56	(word adj line wordline) near3 (Ti titanium) and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 18:56
S96	245	SGT and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S97	536	finfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S98	72	S97 and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S99	243	S96 not S98	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S100	889	(SGT surround\$3 adj gate) and (DRAM memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S101	644	S100 not S96	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S102	755	(257/329).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 09:11
S103	162	S102 and (memory DRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S104	717	(257/300).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 09:11
S105	1	(leslie near3 terrence).in	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11

S106	72	S97 and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S107	42	(maeda near3 shigenobu).in. and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S110	7	S102 and undoped near3 channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S111	107	(438/269).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 09:11
S112	122	S103 not (S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S113	235	S99 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S114	601	S101 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S115	9	vertical adj (transistor channel) not trench and channel near2 undoped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S116	657	(fin adj fet finfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S117	92	S116 and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S118	20	S117 not S98	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S119	657	(finfet fin adj fet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:26

S120	580	S119 not (S103 S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:28
S121	455	S120 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:28
S122	459	S97 not (S103 S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:42
S123	376	S122 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:43
S124	79	S121 not S123	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:40
S125	1502	vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:54
S126	1232	S125 not (S119 S112 S106 S103 S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:55
S127	1173	S126 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:56
S128	573	S127 not trench.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:55
S129	1363	vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM memory adj cell) and capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:54
S130	651	S129 not trench.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:55
S131	489	S130 not (S119 S112 S106 S103 S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:55

S132	464	S131 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 14:59
S133	2063	(257/306).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 10:01
S142	18	(lucien near3 bissey).in.	USPAT	OR	ON	2005/11/09 11:47
S143	20	(thomas near3 voshell).in.	USPAT	OR	ON	2005/11/09 11:48
S144	108	(kevin near3 duesman).in.	USPAT	OR	ON	2005/11/09 11:49
S145	104	S144 not (S143-S142)	USPAT	OR	ON	2005/11/09 11:50
S146	9	undoped near channel and (SGT vmos vertical adj (FET MOSFET transistor channel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 14:11
S147	57	(intrinsic undoped) near2 channel and (SGT vmos vertical adj (FET MOSFET MOS transistor channel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 14:11
S148	58	(intrinsic undoped) near2 channel and (SGT vmos vertical adj (FET MOSFET MISFET MOS transistor channel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 17:08
S149	2	("5451538").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 14:59